Electrostatically actuated mirror-array

- Array of micro mirrors (e.g. 1280x1024 SXGA)
- Produced by Texas Instruments
- "Digital Micro mirror Device""Digital Light Processing"
- Used in projectors, TVs, movie theaters
 - Digital images

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Dimensions of micro mirror array

- Size of mirror: 16μmx16μm, 14μmx14μm, smaller and smaller
- Gap between mirrors 1 μm
- Switch more than 50000 times pr second
- Vacuum packed





Mirror tilting

- Mirror made in reflective aluminium
- Mirror sits on top of Yoke
- Yoke can tilt, supported by torsion hinges
- Yoke can be attracted to left or right electrode by electrostatic forces
- Every electrode for every mirror at the silicon surface can be accessed separately
- The voltage between mirror and electrode is large enough to cause pull-in
- Yoke is mechanically stopped by landing tips (no electric contact)





Fabrication of DMD (from Maluf)



Figure 5.4 Fabrication steps of the Texas Instruments' DMD [2].



Principle of Image Projection

Electrostatic On-Off Control of Mirror Array







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Gap vs. voltage



- Parallell plates, linear spring elastic force
- Normalized gap g/g₀
- Normalized voltage V/V_{PI}



Electrostatic forces

- Forces between charges
- Electric potential Φ
- Laplace equation + boundary conditions (dirichlet)

$$\nabla^2 \Phi = 0$$

Electrostatic field: gradient of potential

$$\vec{\varepsilon} = -\nabla \Phi$$

- Electric force normal to conductor surface
- Charge distribution on surface conductors related to field $q(r) = |\vec{\mathcal{E}}(r)|\mathcal{E}$



Force proportional to electric field

$$\vec{F} = q\vec{E}$$

Forces between parallel plates in capacitor: $-cAV^2$

$$F = \frac{-\varepsilon A V^2}{2g^2}$$

Pull-in of mirror

- Electrostatic force depends on tilt
 Elastic torque: M=k_o O
- Electrostatic torque:

$$\tau = \int_{A} \left(\frac{\varepsilon V^2}{2[g_0 - w(x)]^2} \right) x dx$$

Electrostatic torque varies as $\tau \sim \Theta^2$:



Actuation electrode beneath mirror support

Section view along diagonal



Figure 20.9. Geometry of the DMD mirror.





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Pull-in effect also for mirror



Mechanical and electrostatic equations

 Naviers equation for elastic forces: (isotropic version)

$$(\lambda + \mu)\nabla\nabla \cdot u + \mu\nabla^2 u = 0$$

Poisson equation for electrostatic field: $\nabla^2 \Phi = -\frac{\rho}{\varepsilon}$





Electrostatic bending of beam

- Set up voltage ΔV between beam and substrate
- Beam bend due to electrostatic forces
- Elastic forces tend to pull beam back
- Total force, parallel plates:

$$F_{net} = \frac{-\varepsilon A V^2}{2g^2} + k(g_0 - g)$$



Equilibrium:
$$F_{net} = 0$$



Pull-in of parallel plates with linear spring

Increase ∆V, reach pull-in distance and voltage

$$g_{PI} = 2/3g_0$$

$$V_{PI} = \sqrt{\frac{8kg_0^2}{27\varepsilon A}}$$

- If voltage is larger than pull-in voltage
 no stable solution except g=0
- Senturia section 6.4.3



Figure 6.7. Electrical and spring forces for the voltage-controlled parallel-plate electrostatic actuator, plotted for $V/V_{PI} = 0.8$.



Potential energy of parallel plate capacitor





Charge at zero gap, then...





- Senturia p 127
- Stored energy

$$W(Q) = \int_{0}^{Q} V(Q) dQ$$
$$Q = CV$$
$$W(Q) = Q^{2} / 2C = Q^{2}g / 2\varepsilon A$$

$$E = Q / \varepsilon A$$

$$F = Q^{2}g / 2\varepsilon A$$

$$W(g) = Fg = Q^{2}g / 2\varepsilon A$$

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Pull-in voltage of tilting mirror

Energy

$$W(\theta_0) = \frac{1}{2}CV^2$$

- Torque: negative gradient with respect to θ_0
- Find charge Q on electrodeFind Capacitance

$$\tau = -\frac{1}{2}C(0)V^2 \Big[a_1 + 3a_3\theta_0^2\Big]$$

Restoring torque, torsional spring



Actuation electrode beneath mirror support

Section view along diagonal



itor support

Figure 20.9. Geometry of the DMD mirror.





$$\tau_{elastic} = k_{\theta} \theta_0$$



Pull-in voltage, torsional mirror

Force equilibruim

$$\theta_0 = -\frac{k_\theta}{3a_3C_0V^2} \pm \sqrt{\left(\frac{k_\theta}{3a_3C_0V^2}\right)^2 - \frac{a_1}{3a_3}}$$

$$\left(\frac{k_{\theta}}{3a_3C_0V^2}\right)^2 \ge \frac{a_1}{3a_3}$$

$$V_{PI} = \left(\frac{k_{\theta}^{2}}{3a_{1}a_{3}C_{0}^{2}}\right)^{\frac{1}{4}}$$



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Mirror design with analyzer (tutorial 2)



Figure T3-2 2-D Layout View of Mirror





electrode1 = 20 volts

Charge distribution due to tilt



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electrode2 = 20 volts



Two display principles





Tilting Mirror Optical MEMS

GLV Diffraction Grating MEMS



Silicon Light Machines

- Grating Light Valve
- Electrostatically deflect ribbons
- Distance to wafer $\lambda/4$
- Light is reflected or diffracted
- Diffracted light is projected to screen
- Possible to use pull-in or pullcontrol
- Possible to have one row of ribbon pixels only







Diffraction from a 6-element DLV





GLV linear array of pixels

One line of mirror elements only



Figure 1: A GLV pixel with alternate reflecting ribbons electrostatically deflected to produce a square-well diffraction grating (vertical deflection greatly exaggerated)



Direction of optical scan





Pull in hysteresis of mirrors



Figure 5: To switch a ribbon down requires a voltage differential of V2 volts or more between the ribbon and a bottom electrode. The ribbon will remain down until the voltage differential falls below V1 volts. This ribbon hysteresis offers mechanical memory and zero-power pixel-state retention. Switching time is approximately 20 nanoseconds.



Different colors diffracted to same spot



Figure 7: By using different spacing between ribbons, one can create color-oriented sub-pixels.



Linear elastic force

Partial differential equation for forceelastic displacement (beam):

$$EI\frac{\partial^4 w}{\partial x^4} = q$$

Approximation e.g.

$$F = k w_{\max}$$

Linear relation stress-strain (Always true for single-crystal silicon):

$$\sigma = E\varepsilon$$

Strain is derivative of displacement. May give non-linear relation displacement-strain for large deflections (geometric effect)





Resonant frequency of elastic structure

- Measure resonance frequency in vacuum
- Damping due to fluid flow around moving structure
- Simplified dynamical equation:
 ma + bv + kx = F



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Dynamic equation for beam

$$\rho \frac{\partial^2 u}{\partial t^2} + EI \frac{\partial^4 u}{\partial x^4} = f(x,t) + F / L$$



Couette flow

- Steady viscous flow between parallel plates
- One plate is moving parallel to the other
- Mass conservation, no xdependence on flow velocity
- Streamlines parallel to the walls
- Stationary flow
- No-slip boundary conditions

$$U_x = \frac{y}{h}U$$



Figure 13.4. Illustrating Couette flow

- Shear stress acting on the plate as a result of motion: $\tau_w = -\eta \frac{U}{h}$
- Damping coefficient b

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 $b = \frac{\eta A}{h}$



Squeezed film damping

Displacement of beam, dynamic partial differential equation

$$\rho \frac{\partial^2 u}{\partial t^2} + EI \frac{\partial^4 u}{\partial x^4} = P(x,t) + \frac{F}{L}$$

Flow of gas: Reynolds equation gives pressure in gap

$$12\eta \frac{\partial (Ph)}{\partial t} = \nabla \left[(1 + 6K_n) h^3 P \nabla P \right]$$

Characteristic of solution:

$$P = b \frac{\partial u}{\partial t}$$

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Senturia gives the damping constant for a long beam (L) $b = \frac{96\eta LW}{\pi^4 \alpha^3}$



- Squeeze film number σ
- Relative importance of viscous to spring forces

$$\sigma = \frac{12\eta W^2}{g_0^2 P_0} \omega$$

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